

JC20 Rec'd PCT/PTO 19 SEP 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re U.S. Patent Application of)
SUDA et al.)
Application Number: To Be Assigned)
Filed: Concurrently Herewith)
For: METHOD OF GROWING SEMICONDUCTOR)
CRYSTAL)
ATTORNEY DOCKET NO. HIRA.0204)

Honorable Assistant Commissioner
for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Pursuant to 37 C.F.R. §§ 1.56 and 1.97, this Information Disclosure Statement is submitted in the above-identified National Stage U.S. patent application. A listing of documents to be published on the face of any patent granted from this application is submitted herewith on Form PTO-1449. Any other documents or information submitted for consideration by the Examiner are listed in this paper. A copy of each foreign patent, or each publication or portion thereof listed or herein identified, is submitted herewith.

CERTIFICATION

This Information Disclosure Statement is submitted with the initial filing of the application. Accordingly, no fee is due or payable at this time.

The Examiner is requested to acknowledge consideration of the information provided in this paper in accordance with prescribed procedures.

10/549683

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Please charge any additional fees or credit any overpayments in connection with this paper to Deposit Account No. 08-1480.

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Form PTO 1449 U.S. Department of Commerce Patent and Trademark Office Information Disclosure Statement by Applicant	ATTY. DOCKET NUMBER HIRA.0204	SERIAL NUMBER 10/549683 To be Assigned
APPLICANT SUDA et al.		
FILING DATE Concurrently Herewith		GROUP

U.S. Patent Documents

Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE

Foreign Patent Documents

Examiner Initial	DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
						YES	NO
	09-181355	12/25/95	Japan			Abstract	X
	11-145514	11/5/97	Japan			Abstract	X

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

		International Search Report for Application Serial No. PCT/JP2004/003689 dated July 6, 2004
		Norio Onojima et al., "Molecular-Beam Epitaxial Growth of Insulating AlN on Surface-Controlled 6H-SiC Substrate by HCl Gas Etching", Applied Physics Letters, Volume 80, Number 1 (7 January 2002), pp. 76-78.
EXAMINER	DATE CONSIDERED	
<i>EXAMINER: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant</i>		

PTO1449